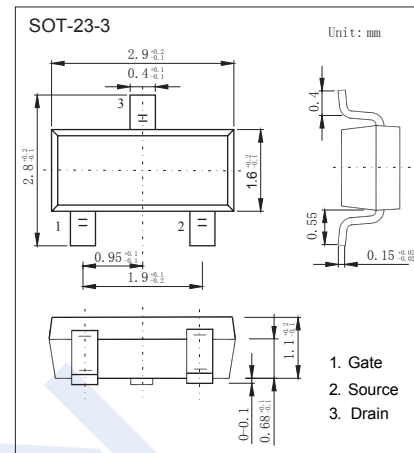
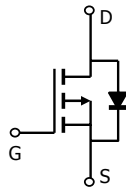


## P-Channel MOSFET

### AO3415 (KO3415)

#### ■ Features

- $V_{DS} (V) = -20V$
- $I_D = -5 A (V_{GS} = -4.5V)$
- $R_{DS(ON)} < 43m\Omega (V_{GS} = -4.5V)$
- $R_{DS(ON)} < 55m\Omega (V_{GS} = -2.5V)$
- $R_{DS(ON)} < 75m\Omega (V_{GS} = -1.8V)$
- $R_{DS(ON)} < 100m\Omega (V_{GS} = -1.5V)$



#### ■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	$V_{DS}$	-20	V
Gate-Source Voltage	$V_{GS}$	$\pm 8$	
Continuous Drain Current	$T_A = 25^\circ C$	-5	A
	$T_A = 70^\circ C$	-4	
Pulsed Drain Current	$I_{DM}$	-30	
Power Dissipation	$T_A = 25^\circ C$	1.5	W
	$T_A = 70^\circ C$	1	
Thermal Resistance.Junction- to-Ambient	$t \leq 10s$	80	$^\circ C/W$
	Steady-State	100	
Thermal Resistance.Junction- to-Lead	$R_{thJL}$	52	
Junction Temperature	$T_J$	150	$^\circ C$
Junction Storage Temperature Range	$T_{stg}$	-55 to 150	

## P-Channel MOSFET

### AO3415 (KO3415)

#### ■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V <sub>DSS</sub>	I <sub>D</sub> =-250 μA, V <sub>GS</sub> =0V	-20			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-20V, V <sub>GS</sub> =0V			-1	μA
		V <sub>DS</sub> =-20V, V <sub>GS</sub> =0V, T <sub>J</sub> =55°C			-5	
Gate-Body leakage current	I <sub>GSS</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =±8V			±0.1	μA
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> I <sub>D</sub> =-250 μA	-0.3		-0.9	V
Static Drain-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-4A			43	mΩ
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-4A T <sub>J</sub> =125°C			59	
		V <sub>GS</sub> =-2.5V, I <sub>D</sub> =-4A			55	
		V <sub>GS</sub> =-1.8V, I <sub>D</sub> =-2A			75	
		V <sub>GS</sub> =-1.5V, I <sub>D</sub> =-1A			100	
On state drain current	I <sub>D(ON)</sub>	V <sub>GS</sub> =-4.5V, V <sub>DS</sub> =-5V	-30			A
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =-5V, I <sub>D</sub> =-4 A		20		S
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> =0V, V <sub>DS</sub> =-10V, f=1MHz	600		905	pF
Output Capacitance	C <sub>oss</sub>		80		150	
Reverse Transfer Capacitance	C <sub>rss</sub>		48		115	
Gate resistance	R <sub>g</sub>	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, f=1MHz	6		20	Ω
Total Gate Charge	Q <sub>g</sub>	V <sub>GS</sub> =-4.5V, V <sub>DS</sub> =-10V, I <sub>D</sub> =-4A	7.4		11	nC
Gate Source Charge	Q <sub>gs</sub>		0.8		1.2	
Gate Drain Charge	Q <sub>gd</sub>		1.3		3.1	
Turn-On DelayTime	t <sub>d(on)</sub>	V <sub>GS</sub> =-4.5V, V <sub>DS</sub> =-10V, R <sub>L</sub> =2.5Ω, R <sub>GEN</sub> =3Ω		13		ns
Turn-On Rise Time	t <sub>r</sub>			9		
Turn-Off DelayTime	t <sub>d(off)</sub>			19		
Turn-Off Fall Time	t <sub>f</sub>			29		
Body Diode Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> =-4A, di/dt=100A/μs	20		32	nC
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>		40		62	
Maximum Body-Diode Continuous Current	I <sub>S</sub>				-2	A
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =-1A, V <sub>GS</sub> =0V			-1	V

\* The static characteristics in Figures 1 to 6 are obtained using <300us pulses, duty cycle 0.5% max.

#### ■ Marking

Marking	AF9T
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## P-Channel MOSFET AO3415 (KO3415)

■ Typical Characteristics

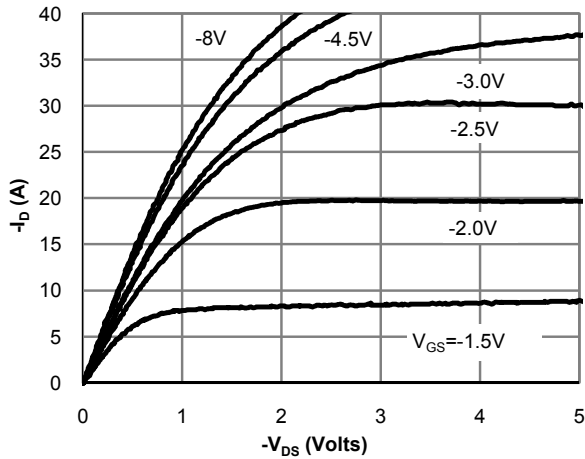


Figure 1: On-Region Characteristics (Note E)

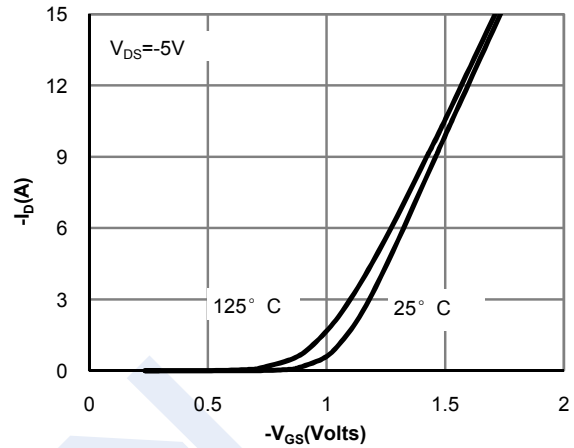


Figure 2: Transfer Characteristics (Note E)

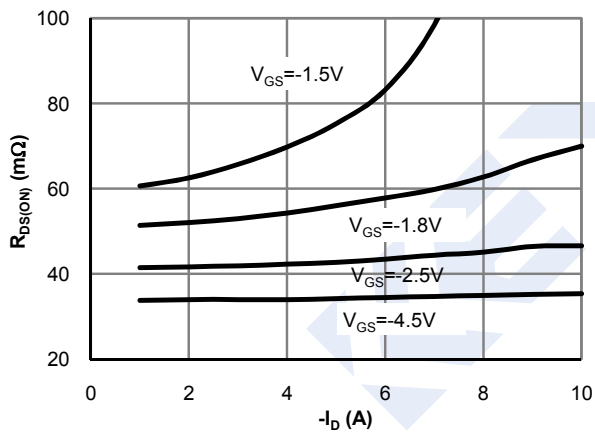


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

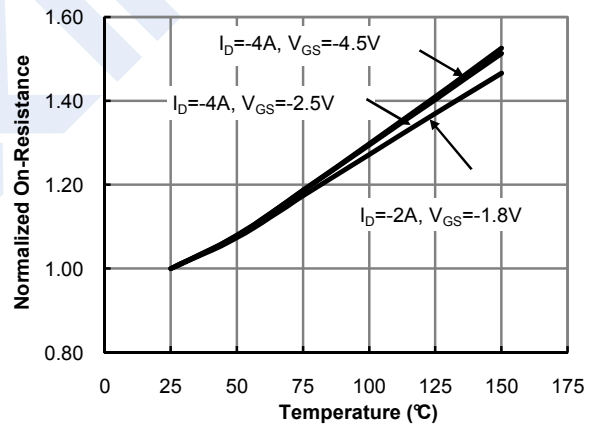


Figure 4: On-Resistance vs. Junction Temperature (Note E)

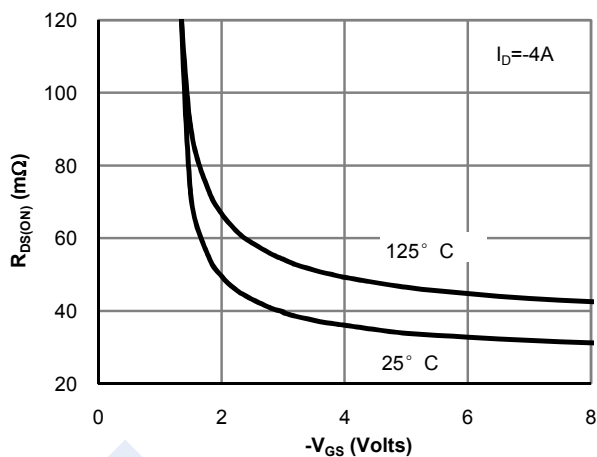


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

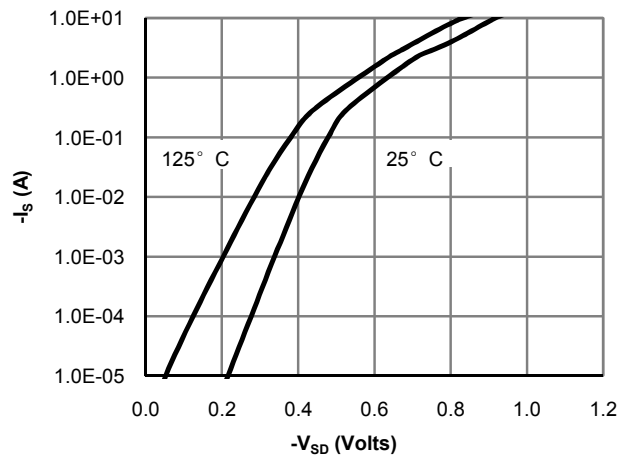


Figure 6: Body-Diode Characteristics (Note E)

# P-Channel MOSFET

## AO3415 (KO3415)

■ Typical Characteristics

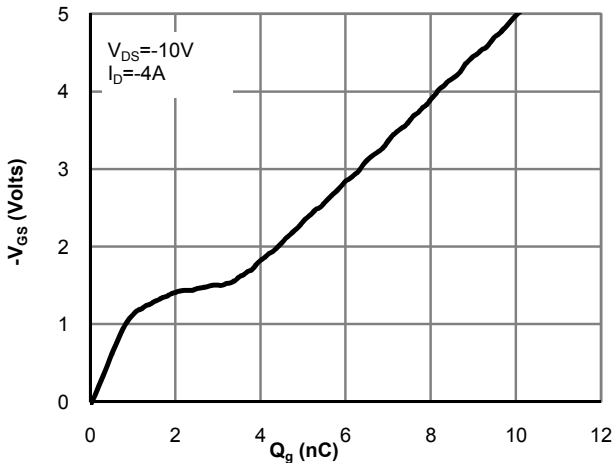


Figure 7: Gate-Charge Characteristics

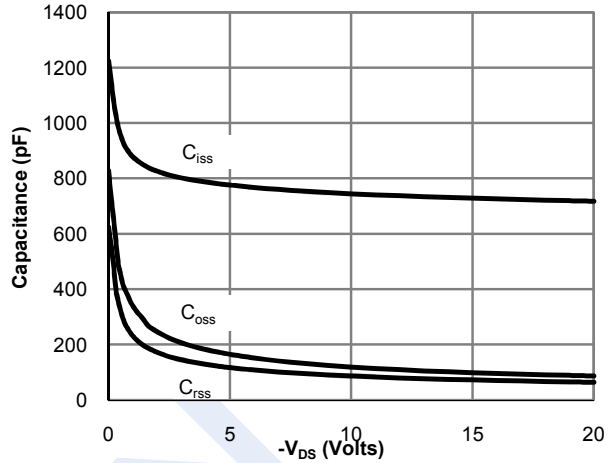


Figure 8: Capacitance Characteristics

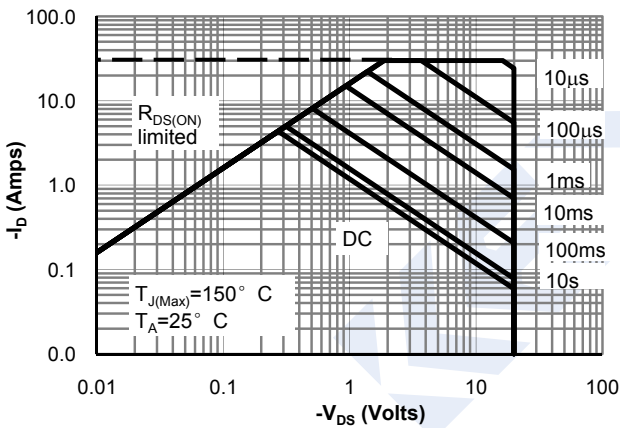


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

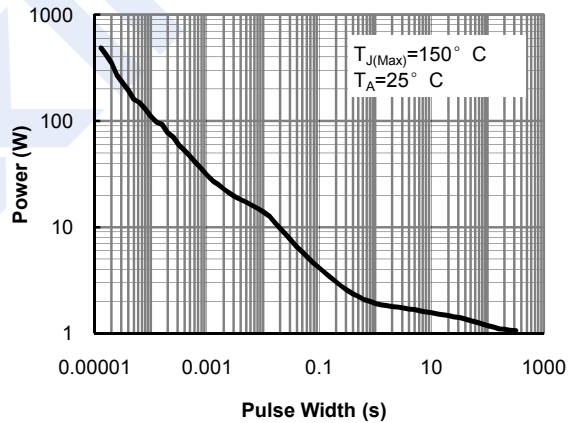


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note F)

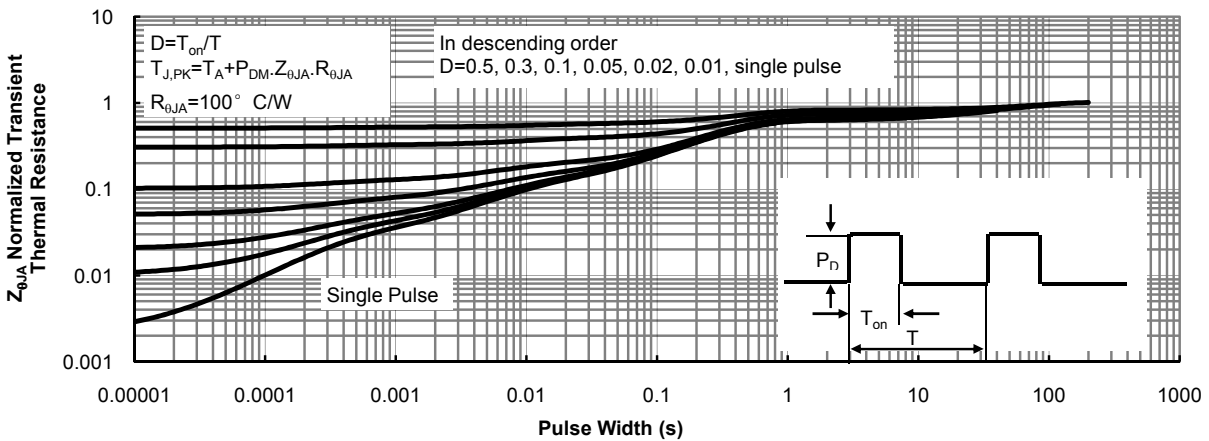


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)